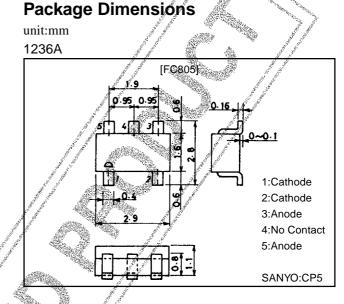


FC805 Silicon Schottky Barrier Diode

# 30V, 500mA Rectifier

## Features

- · Low forward voltage ( $V_F$  max=0.55V).
- $\cdot$  Fast reverse recorvery time (trr max=10ns).
- Composite type with 2 diodes contained in the CP package currently in use, saving the mounting space greatly.
- The FC805 is formed with two chips, each being equivalent to the SB05–03C, placed in one package.



## **Specifications**

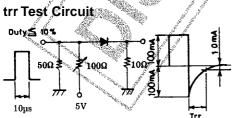
#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol Conditions	Ratings	Unit
Repetitive Peak Reverse Voltage	YRRM	30	V
Nonrepetitive Peak Reverse Surge Voltage	VRSM	35	V
Average Output Current	lo	500	mA
Surge Forward Current	I <sub>FSM</sub> 50MHz sine wave, 1 cycle	5	A
Junction Temperature	the //	-55 to +125	°C
Storage Temperature	Tstg	-55 to +125	°C

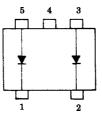
## Electrical Characteristics at Ta = 25°C (Value per element)

Parameter	Symból	Conditions	Ratings			Unit
Falameter	Synthool		min	typ	max	
Reverse Voltage	V <sub>R</sub>	<sup>ν</sup> Ι <sub>R</sub> =150μΑ	30			V
Forward Voltage	V <sub>F</sub>	1 <sub>F</sub> =500mA			0.55	V
Reverse Current	₿ I <sub>B</sub>	V <sub>R</sub> =15V			30	μA
Interteminal Capacitance	ć	V <sub>R</sub> =10V, f=1MHz		16		pF
Reverse Recovery Time	ar trì	I <sub>F</sub> =I <sub>R</sub> =100mA, See specified Test Circuit			10	ns
Thermal Resistance	🖉 Ŗth (j-a)			560		°C/W

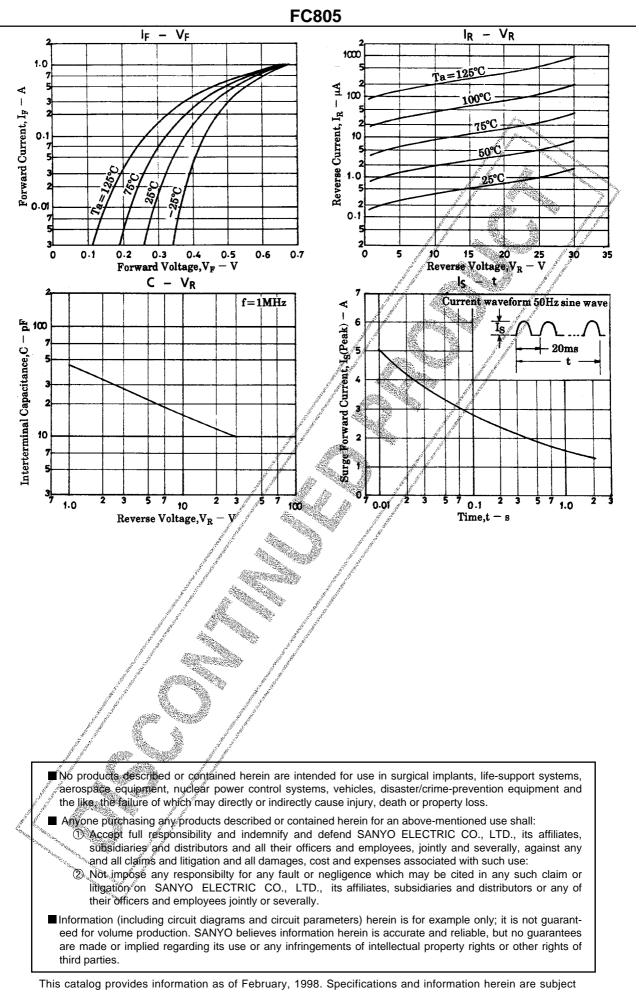
### · Marking:805



#### **Electrical Connection**



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to change without notice.